Martin P Seah

List of Publications by Year
in descending order

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230

papers

10,108

citations

28242

55

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43868

91

g-index

231

all docs

231

docs citations

231

times ranked

6231

citing authors

#	Article	IF	Citations
1	The quantitative analysis of surfaces by XPS: A review. Surface and Interface Analysis, 1980, 2, 222-239.	0.8	404
2	Quantitative Auger electron spectroscopy and electron ranges. Surface Science, 1972, 32, 703-728.	0.8	390
3	Adsorption-induced interface decohesion. Acta Metallurgica, 1980, 28, 955-962.	2.1	339
4	XPS: Energy calibration of electron spectrometers. 1â€”An absolute, traceable energy calibration and the provision of atomic reference line energies. Surface and Interface Analysis, 1984, 6, 95-106.	0.8	269
5	Post-1989 calibration energies for X-ray photoelectron spectrometers and the 1990 Josephson constant. Surface and Interface Analysis, 1989, 14, 488-488.	0.8	218
6	Interface adsorption, embrittlement and fracture in metallurgy. Surface Science, 1975, 53, 168-212.	0.8	206
7	Summary of ISO/TC 201 Standard: VII ISO 15472 : 2001?surface chemical analysis?x-ray photoelectron spectrometers?calibration of energy scales. Surface and Interface Analysis, 2001, 31, 721-723.	0.8	200
8	Ultrathin SiO2 on Si II. Issues in quantification of the oxide thickness. Surface and Interface Analysis, 2002, 33, 640-652.	0.8	195
9	Grain boundary segregation and the T-t dependence of temper brittleness. Acta Metallurgica, 1977, 25, 345-357.	2.1	176
10	The determination of atomic force microscope cantilever spring constants via dimensional methods for nanomechanical analysis. Nanotechnology, 2005, 16, 1666-1680.	1.3	166
11	AES: Energy calibration of electron spectrometers. I?an absolute, traceable energy calibration and the provision of atomic reference line energies. Surface and Interface Analysis, 1990, 15, 293-308.	0.8	165
12	Quantitative XPS. Journal of Electron Spectroscopy and Related Phenomena, 2001, 120, 93-111.	0.8	163
13	Data compilations: their use to improve measurement certainty in surface analysis by aes and xps. Surface and Interface Analysis, 1986, 9, 85-98.	0.8	153
14	Pure element sputtering yields using 500â€“1000 eV argon ions. Thin Solid Films, 1981, 81, 279-287.	0.8	152
15	Organic Depth Profiling of a Nanostructured Delta Layer Reference Material Using Large Argon Cluster Ions. Analytical Chemistry, 2010, 82, 98-105.	3.2	152
16	Quantification issues in the identification of nanoscale regions of homopolymers using modulus measurement via AFM nanoindentation. Applied Surface Science, 2005, 252, 1915-1933.	3.1	147
17	Critical review of the current status of thickness measurements for ultrathin SiO2 on Si Part V: Results of a CCQM pilot study. Surface and Interface Analysis, 2004, 36, 1269-1303.	0.8	138
18	Universal Equation for Argon Gas Cluster Sputtering Yields. Journal of Physical Chemistry C, 2013, 117, 12622-12632.	1.5	134

#	ARTICLE	IF	CITATIONS
19	XPS reference procedure for the accurate intensity calibration of electron spectrometers? results of a BCR intercomparison co-sponsored by the VAMAS SCA TWA. Surface and Interface Analysis, 1993, 20, 243-266.	0.8	132
20	Argon Cluster Ion Beams for Organic Depth Profiling: Results from a VAMAS Interlaboratory Study. Analytical Chemistry, 2012, 84, 7865-7873.	3.2	129
21	Quantitative Molecular Depth Profiling of Organic Delta-Layers by C60 Ion Sputtering and SIMS. Journal of Physical Chemistry B, 2008, 112, 2596-2605.	1.2	119
22	Ion detection efficiency in SIMS:. International Journal of Mass Spectrometry, 2000, 202, 217-229.	0.7	117
23	Quantitative prediction of surface segregation. Journal of Catalysis, 1979, 57, 450-457.	3.1	114
24	An accurate semi-empirical equation for sputtering yields I: for argon ions. Surface and Interface Analysis, 2005, 37, 444-458.	0.8	112
25	The depth dependence of the depth resolution in composition-depth profiling with Auger Electron Spectroscopy. Surface and Interface Analysis, 1983, 5, 33-37.	0.8	111
26	Ultrathin SiO2 on Si IV. Intensity measurement in XPS and deduced thickness linearity. Surface and Interface Analysis, 2003, 35, 515-524.	0.8	109
27	Simple universal curve for the energyâ€dependent electron attenuation length for all materials. Surface and Interface Analysis, 2012, 44, 1353-1359.	0.8	106
28	Sputtering yields of compounds using argon ions. Journal Physics D: Applied Physics, 2010, 43, 253001.	1.3	105
29	Slow electron scattering from metals. Surface Science, 1969, 17, 132-160.	0.8	99
30	Quantitative AES and XPS: Determination of the electron spectrometer transmission function and the detector sensitivity energy dependencies for the production of true electron emission spectra in AES and XPS. Surface and Interface Analysis, 1990, 15, 751-766.	0.8	97
31	Characterization of a high depth-resolution tantalum pentoxide sputter profiling reference material. Surface and Interface Analysis, 1983, 5, 199-209.	0.8	94
32	Simplified equations for correction parameters for elastic scattering effects in AES and XPS forQ, ? and attenuation lengths. Surface and Interface Analysis, 2001, 31, 835-846.	0.8	87
33	A system for the intensity calibration of electron spectrometers. Journal of Electron Spectroscopy and Related Phenomena, 1995, 71, 191-204.	0.8	86
34	Random uncertainties in AES and XPS: I: Uncertainties in peak energies, intensities and areas derived from peak synthesis. Surface and Interface Analysis, 1992, 18, 345-360.	0.8	84
35	Static SIMS: towards unfragmented mass spectra â€” the G-SIMS procedure. Applied Surface Science, 2000, 161, 465-480.	3.1	82
36	XPS: Energy calibration of electron spectrometers. 2â€"Results of an interlaboratory comparison. Surface and Interface Analysis, 1984, 6, 107-115.	0.8	76

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37	Modelling of nanomechanical nanoindentation measurements using an AFM or nanoindenter for compliant layers on stiffer substrates. Nanotechnology, 2006, 17, 5283-5292.	1.3	76
38	The statistical sputtering contribution to resolution in concentration-depth profiles. Thin Solid Films, 1981, 81, 239-246.	0.8	74
39	A review of the analysis of surfaces and thin films by AES and XPS. Vacuum, 1984, 34, 463-478.	1.6	73
40	An accurate and simple universal curve for the energyâ€dependent electron inelastic mean free path. Surface and Interface Analysis, 2012, 44, 497-503.	0.8	73
41	Depth resolution in composition profiles by ion sputtering and surface analysis for single-layer and multilayer structures on real substrates. Thin Solid Films, 1981, 81, 257-270.	0.8	72
42	Background subtraction. Surface Science, 1999, 420, 285-294.	0.8	72
43	Quantitative XPS: The calibration of spectrometer intensityâ€"energy response functions. 1â€"The establishment of reference procedures and instrument behaviour. Surface and Interface Analysis, 1984, 6, 230-241.	0.8	71
44	TOF-SIMS: Accurate mass scale calibration. Journal of the American Society for Mass Spectrometry, 2006, 17, 514-523.	1.2	71
45	The quartz crystal microbalance; radial/polar dependence of mass sensitivity both on and off the electrodes. Measurement Science and Technology, 1990, 1, 544-555.	1.4	70
46	Channel electron multipliers: quantitative intensity measurementâ€"efficiency, gain, linearity and bias effects. Journal of Electron Spectroscopy and Related Phenomena, 1990, 50, 137-157.	0.8	68
47	Electron flood gun damage in the analysis of polymers and organics in time-of-flight SIMS. Applied Surface Science, 2002, 187, 89-100.	3.1	66
48	Grain boundary activity measurements by auger electron spectroscopy. Scripta Metallurgica, 1972, 6, 1007-1012.	1.2	64
49	Quantitative AES IX and quantitative XPS II: Auger and x-ray photoelectron intensities and sensitivity factors from spectral digital databases reanalysed using a REELS database. Surface and Interface Analysis, 2001, 31, 778-795.	0.8	63
50	An accurate semi-empirical equation for sputtering yields, II: for neon, argon and xenon ions. Nuclear Instruments & Methods in Physics Research B, 2005, 229, 348-358.	0.6	62
51	AES: Accurate intensity calibration of electron spectrometersâ€"results of a BCR interlaboratory comparison co-sponsored by the VAMAS SCA TWP. Surface and Interface Analysis, 1991, 17, 855-874.	0.8	61
52	Quantitative characterization of defect size in graphene using Raman spectroscopy. Applied Physics Letters, 2014, 105, .	1.5	61
53	Quantitative Auger electron spectroscopy; A comparison of techniques for adsorbed tin on iron. Surface Science, 1973, 40, 595-608.	0.8	60
54	Background subtraction. Surface Science, 2000, 461, 1-15.	0.8	60

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55	Peptide Fragmentation and Surface Structural Analysis by Means of ToF-SIMS Using Large Cluster Ion Sources. Analytical Chemistry, 2016, 88, 3592-3597.	3.2	59
56	Quantitative XPS: The calibration of spectrometer intensityâ€"energy response functions. 2â€"Results of interlaboratory measurements for commercial instruments. Surface and Interface Analysis, 1984, 6, 242-254.	0.8	58
57	Developing Repeatable Measurements for Reliable Analysis of Molecules at Surfaces Using Desorption Electrospray Ionization. Analytical Chemistry, 2009, 81, 2286-2293.	3.2	55
58	Ultrathin SiO2 on Si. VII. Angular accuracy in XPS and an accurate attenuation length. Surface and Interface Analysis, 2005, 37, 731-736.	0.8	51
59	Optimized depth resolution in ion-sputtered and lapped compositional profiles with Auger electron spectroscopy. Thin Solid Films, 1981, 75, 67-86.	0.8	50
60	Site competition in surface segregation. Surface Science, 1975, 53, 272-285.	0.8	48
61	AES of bulk insulators â€" control and characterisation of the surface charge. Journal of Electron Spectroscopy and Related Phenomena, 2000, 109, 291-308.	0.8	48
62	The surface analysis of insulators by SIMS: Charge neutralization and stabilization of the surface potential. Surface and Interface Analysis, 1981, 3, 157-160.	0.8	45
63	Validation and accuracy of software for peak synthesis in XPS. Journal of Electron Spectroscopy and Related Phenomena, 1998, 95, 71-93.	0.8	45
64	Intensity and energy calibration in AES: The effect of analyser modulation. Journal of Electron Spectroscopy and Related Phenomena, 1983, 32, 73-86.	0.8	43
65	Topography and Field Effects in Secondary Ion Mass Spectrometry â€" Part I: Conducting Samples. Journal of the American Society for Mass Spectrometry, 2011, 22, 1718-28.	1.2	43
66	Surface science in metallurgy. Surface Science, 1979, 80, 8-23.	0.8	41
67	Topography and field effects in the quantitative analysis of conductive surfaces using ToF-SIMS. Applied Surface Science, 2008, 255, 1560-1563.	3.1	41
68	The ultra-high resolution depth profiling reference material â€" Ta2O5 anodically grown on Ta. Surface Science, 1984, 139, 549-557.	0.8	40
69	Characterisation of computer differentiation of spectra in AES and its relation to differentiation by the modulation technique. Journal of Physics E: Scientific Instruments, 1983, 16, 848-857.	0.7	39
70	Stability of reference masses. IV: Growth of carbonaceous contamination on platinum-iridium alloy surfaces, and cleaning by UV/ozone treatment. Metrologia, 1996, 33, 507-532.	0.6	39
71	Ultrathin SiO2 on Si: III mapping the layer thickness efficiently by XPS. Surface and Interface Analysis, 2002, 33, 960-963.	0.8	39
72	Ultraâ€•thin SiO₂ on Si IX: absolute measurements of the amount of silicon oxide as a thickness of SiO₂ on Si. Surface and Interface Analysis, 2009, 41, 430-439.	0.8	39

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73	An intercomparison of absolute measurements of the oxygen and tantalum thickness of tantalum pentoxide reference materials, BCR 261, by six laboratories. Nuclear Instruments & Methods in Physics Research B, 1988, 30, 140-151.	0.6	38
74	VAMAS Interlaboratory Study for Desorption Electrospray Ionization Mass Spectrometry (DESI MS) Intensity Repeatability and Constancy. Analytical Chemistry, 2014, 86, 9603-9611.	3.2	38
75	Quantitative AES and XPS: convergence between theory and experimental databases. Journal of Electron Spectroscopy and Related Phenomena, 1999, 100, 55-73.	0.8	37
76	Ultrathin SiO2 on Si. VI. Evaluation of uncertainties in thickness measurement using XPS. Surface and Interface Analysis, 2005, 37, 300-309.	0.8	37
77	Analysis of cluster ion sputtering yields: correlation with the thermal spike model and implications for static secondary ion mass spectrometry. Surface and Interface Analysis, 2007, 39, 634-643.	0.8	37
78	Quantification and measurement by Auger electron spectroscopy and X-ray photoelectron spectroscopy. Vacuum, 1986, 36, 399-407.	1.6	36
79	Stability of Reference Masses II: The Effect of Environment and Cleaning Methods on the Surfaces of Stainless Steel and Allied Materials. Metrologia, 1994, 31, 93-108.	0.6	36
80	Use of a â€œBETâ€•analogue equation to describe grain boundary segregation. Scripta Metallurgica, 1973, 7, 735-737.	1.2	35
81	Roughness contributions to resolution in ion sputter depth profiles of polycrystalline metal films. Thin Solid Films, 1984, 115, 203-216.	0.8	35
82	Nanoindentation measurement of Youngâ€™s modulus for compliant layers on stiffer substrates including the effect of Poissonâ€™s ratios. Nanotechnology, 2009, 20, 145708.	1.3	34
83	Sputtering Yields of Gold Nanoparticles by C₆₀ Ions. Journal of Physical Chemistry C, 2012, 116, 9311-9318.	1.5	34
84	Slow electron scattering from metals. Surface Science, 1969, 17, 181-213.	0.8	33
85	Approaches to analyzing insulators with Auger electron spectroscopy: Update and overview. Journal of Electron Spectroscopy and Related Phenomena, 2010, 176, 80-94.	0.8	33
86	Universal Equation for Argon Cluster Size-Dependence of Secondary Ion Spectra in SIMS of Organic Materials. Journal of Physical Chemistry C, 2014, 118, 12862-12872.	1.5	33
87	Atomic mixing and electron range effects in ultrahighâ€•resolution profiles of the Ta2O5/Ta interface by argon sputtering with Auger electron spectroscopy. Journal of Applied Physics, 1984, 56, 2106-2113.	1.1	31
88	Reassessment of energy transfers in the quasielastic scattering of 250â€“3000 eV electrons at surfaces. Physical Review B, 1993, 47, 9836-9839.	1.1	31
89	G-SIMS of crystallisable organics. Applied Surface Science, 2003, 203-204, 551-555.	3.1	31
90	Ultra-thin SiO2 on Si VIII. Accuracy of method, linearity and attenuation lengths for XPS. Surface and Interface Analysis, 2007, 39, 512-518.	0.8	31

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91	Improved methods and uncertainty analysis in the calibration of the spring constant of an atomic force microscope cantilever using static experimental methods. Measurement Science and Technology, 2009, 20, 125501.	1.4	31
92	Attenuation lengths in organic materials. Surface and Interface Analysis, 2011, 43, 744-751.	0.8	31
93	Slow electron scattering from metals. Surface Science, 1969, 17, 161-180.	0.8	30
94	Linearity in electron counting and detection systems. Surface and Interface Analysis, 1992, 18, 240-246.	0.8	30
95	Quantitative AES: Determination of the effects of the relative orientations of the sample, electron gun and spectrometer on the direct spectrum shape for the establishment of standard reference spectra. Surface and Interface Analysis, 1989, 14, 823-834.	0.8	29
96	Stability of Reference Masses I: Evidence for Possible Variations in the Mass of Reference Kilograms Arising from Mercury Contamination. Metrologia, 1994, 31, 21-26.	0.6	29
97	Cluster ion sputtering: molecular ion yield relationships for different cluster primary ions in static SIMS of organic materials. Surface and Interface Analysis, 2007, 39, 890-897.	0.8	29
98	Analysis Of The Interface And Its Position In C60n+ Secondary Ion Mass Spectrometry Depth Profiling. Analytical Chemistry, 2009, 81, 75-79.	3.2	29
99	Topography and field effects in secondary ion mass spectrometry Part II: insulating samples. Surface and Interface Analysis, 2012, 44, 238-245.	0.8	29
100	AES and XPS depth profiling certified reference material. Surface and Interface Analysis, 1984, 6, 92-93.	0.8	28
101	Organic molecule characterizationâ€”G-SIMS. Applied Surface Science, 2004, 231-232, 224-229.	3.1	28
102	Imaging Gâ€SIMS: a novel bismuthâ€manganese source emitter. Rapid Communications in Mass Spectrometry, 2008, 22, 2602-2608.	0.7	28
103	VAMAS interlaboratory study on organic depth profiling. Surface and Interface Analysis, 2011, 43, 1240-1250.	0.8	28
104	Surface segregation as a guide to grain boundary segregation. Scripta Metallurgica, 1975, 9, 583-586.	1.2	27
105	Channel electron multiplier efficiencies: the effect of the pulse height distribution on spectrum shape in auger electron spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 1989, 48, 209-218.	0.8	27
106	AES: energy calibration of electron spectrometers. IV. A re-evaluation of the reference energies. Journal of Electron Spectroscopy and Related Phenomena, 1998, 97, 235-241.	0.8	27
107	Smoothing and the signal-to-noise ratio of peaks in electron spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 1989, 48, 43-54.	0.8	26
108	Depth Profiling and Melting of Nanoparticles in Secondary Ion Mass Spectrometry (SIMS). Journal of Physical Chemistry C, 2013, 117, 16042-16052.	1.5	26

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109	Angle Dependence of Argon Gas Cluster Sputtering Yields for Organic Materials. Journal of Physical Chemistry B, 2015, 119, 3297-3303.	1.2	26
110	Method to determine the analysis area of xâ€ray photoelectron spectrometersâ€"illustrated by a Perkinâ€"Elmer PHI 550 ESCA/SAM. Review of Scientific Instruments, 1985, 56, 703-711.	0.6	25
111	Towards a single recommended optimal convolutional smoothing algorithm for electron and other spectroscopies. Journal of Physics E: Scientific Instruments, 1988, 21, 351-363.	0.7	25
112	Scattering in electron spectrometers, diagnosis and avoidance. I. Concentric hemispherical analysers. Surface and Interface Analysis, 1993, 20, 865-875.	0.8	25
113	Effective dead time in pulse counting systems. Surface and Interface Analysis, 1995, 23, 729-732.	0.8	25
114	Quantitative aes: the problems of the energy dependent phase shift and modulation amplitude and of the non-ideal behaviour of the channel electron multiplier. Journal of Electron Spectroscopy and Related Phenomena, 1987, 42, 255-269.	0.8	24
115	Signal linearity in XPS counting systems. Journal of Electron Spectroscopy and Related Phenomena, 1999, 104, 73-89.	0.8	24
116	Quantitative AES: The establishment of a standard reference spectrum for the accurate determination of spectrometer transmission functions. Surface and Interface Analysis, 1988, 12, 105-109.	0.8	23
117	Identification of complex molecules at surfaces: G-SIMS and SMILES fragmentation pathways. International Journal of Mass Spectrometry, 2008, 272, 38-47.	0.7	23
118	On the applicability of XPS for quantitative total organic and elemental carbon analysis of airborne particulate matter. Atmospheric Environment, 2008, 42, 3888-3891.	1.9	23
119	Simplified drift characterization in scanning probe microscopes using a simple two-point method. Measurement Science and Technology, 2009, 20, 095103.	1.4	23
120	Cluster Primary Ion Sputtering: Secondary Ion Intensities in Static SIMS of Organic Materials. Journal of Physical Chemistry C, 2010, 114, 5351-5359.	1.5	23
121	Topography effects and monatomic ion sputtering of undulating surfaces, particles and large nanoparticles: Sputtering yields, effective sputter rates and topography evolution. Surface and Interface Analysis, 2012, 44, 208-218.	0.8	23
122	The matrix effect in secondary ion mass spectrometry. Applied Surface Science, 2018, 439, 605-611.	3.1	23
123	Resolution parameters for model functions used in surface analysis. Surface and Interface Analysis, 2002, 33, 950-953.	0.8	21
124	Sputtering Yields for Gold Using Argon Gas Cluster Ion Beams. Journal of Physical Chemistry C, 2012, 116, 23735-23741.	1.5	21
125	Depth resolution at organic interfaces sputtered by argon gas cluster ions: the effect of energy, angle and cluster size. Analyst, The, 2015, 140, 6508-6516.	1.7	21
126	An intercomparison of tantalum pentoxide reference studies. Nuclear Instruments & Methods in Physics Research B, 1988, 30, 128-139.	0.6	20

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127	Auger electron spectroscopy: Method for the accurate measurement of signal and noise and a figure of merit for the performance of AES instrument sensitivity. Review of Scientific Instruments, 1988, 59, 217-227.	0.6	20
128	Mass Spectrometry and Informatics: Distribution of Molecules in the PubChem Database and General Requirements for Mass Accuracy in Surface Analysis. Analytical Chemistry, 2011, 83, 3239-3243.	3.2	20
129	An atomic standard to calibrate analyser modulation in AES. Journal of Electron Spectroscopy and Related Phenomena, 1983, 32, 87-97.	0.8	19
130	Summary of ISO/TC 201 Standard: VIII, ISO 18115:2001?Surface chemical analysis?Vocabulary. Surface and Interface Analysis, 2001, 31, 1048-1049.	0.8	19
131	Sputtering Yields for Mixtures of Organic Materials Using Argon Gas Cluster Ions. Journal of Physical Chemistry B, 2015, 119, 13433-13439.	1.2	19
132	The intergranular fragility index â€" an engineering materials parameter. Materials Science and Engineering, 1980, 42, 233-244.	0.1	18
133	Energy and spatial dependence of the electron detection efficiencies of single channel electron multipliers used in electron spectroscopy. Review of Scientific Instruments, 1991, 62, 62-68.	0.6	18
134	Random uncertainties in AES and XPS: II: Quantification using either relative or absolute measurements. Surface and Interface Analysis, 1992, 18, 361-367.	0.8	18
135	Background subtraction III. Surface Science, 2001, 471, 185-202.	0.8	18
136	Investigating the difficulty of eliminating flood gun damage in TOF-SIMS. Applied Surface Science, 2003, 203-204, 600-604.	3.1	18
137	Linearity of the instrumental intensity scale in TOFâ€SIMSâ€"a VAMAS interlaboratory study. Surface and Interface Analysis, 2012, 44, 1-14.	0.8	18
138	Temperature, roughness and depth resolution in ion sputter profiles. Surface Science, 1985, 150, 273-288.	0.8	17
139	G-SIMS-FPM: Molecular structure at surfacesâ€"a combined positive and negative secondary ion study. Applied Surface Science, 2006, 252, 6601-6604.	3.1	17
140	Nanomechanical measurements of hair as an example of micro-fibre analysis using atomic force microscopy nanoindentation. Ultramicroscopy, 2012, 114, 38-45.	0.8	17
141	Scattering in electron spectrometers, diagnosis and avoidance. II. Cylindrical mirror analysers. Surface and Interface Analysis, 1993, 20, 876-890.	0.8	16
142	Static SIMS: Surface charge stabilization of insulators for highly repeatable spectra when using a quadrupole mass spectrometer. Surface and Interface Analysis, 1995, 23, 191-203.	0.8	16
143	Stability of Reference Masses III: Mechanism and Long-term Effects of Mercury Contamination on Platinum-Iridium Mass Standards. Metrologia, 1995, 31, 375-388.	0.6	15
144	Repeatable intensity calibration of an X-ray photoelectron spectrometer. Journal of Electron Spectroscopy and Related Phenomena, 2006, 151, 178-181.	0.8	15

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145	Electron Flood Gun Damage Effects in 3D Secondary Ion Mass Spectrometry Imaging of Organics. Journal of the American Society for Mass Spectrometry, 2014, 25, 1565-1571.	1.2	15
146	Semiempirical Rules To Determine Drug Sensitivity and Ionization Efficiency in Secondary Ion Mass Spectrometry Using a Model Tissue Sample. Analytical Chemistry, 2016, 88, 11028-11036.	3.2	15
147	The temperature dependence of the energy of leed intensity peaks and its effect on the surface debye temperature. Physics Letters, Section A: General, Atomic and Solid State Physics, 1969, 30, 263-264.	0.9	14
148	Fluence, flux, current and current density measurement in faraday cups for surface analysis. Surface and Interface Analysis, 1995, 23, 248-258.	0.8	14
149	Degradation of poly(vinyl chloride) and nitrocellulose in XPS. Surface and Interface Analysis, 2003, 35, 906-913.	0.8	14
150	Modelling of surface nanoparticle inclusions for nanomechanical measurements by an AFM or nanoindenter: spatial issues. Nanotechnology, 2012, 23, 165704.	1.3	14
151	Sampling Depths, Depth Shifts, and Depth Resolutions for Bi_{<i>n</i>}⁺ Ion Analysis in Argon Gas Cluster Depth Profiles. Journal of Physical Chemistry B, 2016, 120, 2604-2611.	1.2	14
152	Signal-to-noise ratio assessment and measurement in spectroscopies with particular reference to Auger and X-ray photoelectron spectroscopies. Journal of Electron Spectroscopy and Related Phenomena, 1993, 61, 291-308.	0.8	13
153	AES: energy calibration of electron spectrometers. III â€" General calibration rules. Journal of Electron Spectroscopy and Related Phenomena, 1997, 83, 197-208.	0.8	13
154	Esca microscope â€" a new approach for imaging in XPS. Journal of Electron Spectroscopy and Related Phenomena, 1987, 42, 359-363.	0.8	12
155	Summary of ISO/TC 201 Standard XI. ISO 17974:2002?Surface chemical analysis?High-resolution Auger electron spectrometers?Calibration of energy scales for elemental and chemical-state analysis. Surface and Interface Analysis, 2003, 35, 327-328.	0.8	12
156	Artifacts in the sputtering of inorganics by C60n+. Applied Surface Science, 2008, 255, 934-937.	3.1	12
157	Cluster primary ion sputtering: correlations in secondary ion intensities in TOF SIMS. Surface and Interface Analysis, 2011, 43, 228-235.	0.8	12
158	AES: Energy calibration of electron spectrometers. II?results of a BCRinterlaboratory comparison co-sponsored by the vamas SCS TWP. Surface and Interface Analysis, 1990, 15, 309-322.	0.8	11
159	Versailles project on advanced materials and standards study of intensity stability of cylindrical mirror analyser-based Auger electron spectrometers. Journal of Electron Spectroscopy and Related Phenomena, 1992, 58, 345-357.	0.8	11
160	Static SIMS: metastable decay and peak intensities. Applied Surface Science, 1999, 144-145, 26-30.	3.1	11
161	Reference data for Auger electron spectroscopy and X-ray photoelectron spectroscopy combined. Applied Surface Science, 1999, 144-145, 161-167.	3.1	11
162	Summary of ISO/TC 201 Standard XII. ISO 17973:2002?Surface chemical analysis?Medium-resolution Auger electron spectrometers?Calibration of energy scales for elemental analysis. Surface and Interface Analysis, 2003, 35, 329-330.	0.8	11

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163	Relationships between cluster secondary ion mass intensities generated by different cluster primary ions. Journal of the American Society for Mass Spectrometry, 2010, 21, 370-377.	1.2	11
164	Method for the alignment of samples and the attainment of ultra-high-resolution depth profiles in Auger electron spectroscopy. Surface and Interface Analysis, 1990, 15, 254-258.	0.8	10
165	Erratum to â€œAn accurate semi-empirical equation for sputtering yields, II: for neon, argon and xenon ionsâ€•[Nucl. Instr. and Meth. B 229 (2005) 348â€“358]. Nuclear Instruments & Methods in Physics Research B, 2005, 239, 286-287.	0.6	10
166	Identification and separation of protein, contaminant and substrate peaks using gentleâ€•secondary ion mass spectrometry and the <i>g</i>â€•ogram. Rapid Communications in Mass Spectrometry, 2012, 26, 2815-2821.	0.7	10
167	Argon cluster size-dependence of sputtering yields of polymers: molecular weights and the universal equation. Surface and Interface Analysis, 2015, 47, 169-172.	0.8	10
168	Identification of surface plasmons excited in that flat region of a single crystal surface monitored by LEED. Surface Science, 1971, 24, 357-369.	0.8	9
169	A verification of the relativistic correction for electro-static electron spectrometers. Journal of Electron Spectroscopy and Related Phenomena, 1985, 35, 145-153.	0.8	9
170	Model calculations of the electron-optical properties of compact Faraday cups. Journal of Physics E: Scientific Instruments, 1989, 22, 242-249.	0.7	9
171	The alignment of spectrometers and quantitative measurements in X-ray photoelectron spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 1997, 87, 159-167.	0.8	9
172	Summary of ISO/TC 201 Standard: XXIV, ISO 24237:2005â€”surface chemical analysisâ€”X-ray photoelectron spectroscopyâ€”repeatability and constancy of intensity scale. Surface and Interface Analysis, 2007, 39, 370-372.	0.8	9
173	The energy and temperature dependence of LEED intensity peak widths. Physics Letters, Section A: General, Atomic and Solid State Physics, 1969, 30, 250-251.	0.9	8
174	Savitzky and Golay differentiation in AES. Applied Surface Science, 1996, 93, 273-280.	3.1	8
175	Static SIMS: ion detection efficiencies in a channel electron multiplier. Applied Surface Science, 1999, 144-145, 113-117.	3.1	8
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